

IFN5911, IFN5912 Dual Matched N-Channel JFET

Features

- InterFET [N0030L Geometry](#)
- Low Noise: 4.0 nV/ $\sqrt{\text{Hz}}$ Typical
- Low Leakage: 10pA Typical
- Low Input Capacitance: 5.0 pF Typical
- RoHS Compliant
- SMT, TH, and Bare Die Package options.

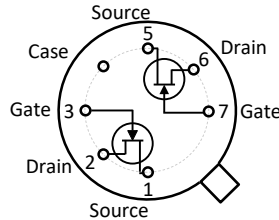
Applications

- VHF Amplifiers
- Wideband Differential Amplifiers

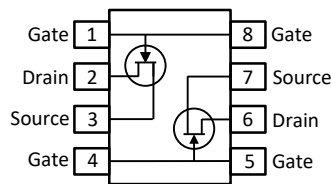
Description

The -25V InterFET IFN5911 and IFN 5912 JFET's are targeted for wideband differential amplifiers. Gate leakages are less than 10pA at room temperatures. The TO-78 package is hermetically sealed and suitable for military applications.

TO-78 Bottom View



SOIC8 Top View



Product Summary

| Parameters | IFN5911 Min | IFN5912 Min | Unit |
|--|-------------|-------------|---------|
| BV_{GSS} Gate to Source Breakdown Voltage | -25 | -25 | V |
| I_{DSS} Drain to Source Saturation Current | 7 | 7 | mA |
| $V_{GS(off)}$ Gate to Source Cutoff Voltage | -1 | -1 | V |
| G_{FS} Forward Transconductance | 3000 | 3000 | μS |

Ordering Information Custom Part and Binning Options Available

| Part Number | Description | Case | Packaging |
|------------------------|---|-------|-------------------------------------|
| IFN5911; IFN5912 | Through-Hole | TO-78 | Bulk |
| SMP5911; SMP5912 | Surface Mount | SOIC8 | Bulk |
| SMP5911; SMP5912 | 7" Tape and Reel: Max 500 Pieces 13" Tape and Reel: Max 2,500 Pieces | SOIC8 | Minimum 500 Pieces Tape and Reel |
| IFN5911COT; IFN5912COT | Chip Orientated Tray (COT Waffle Pack) | COT | 400/Waffle Pack |
| IFN5911CFT; IFN5912CFT | Chip Face-up Tray (CFT Waffle Pack) | CFT | 400/Waffle Pack |



Disclaimer: It is the Buyers responsibility for designing, validating and testing the end application under all field use cases and extreme use conditions. Guaranteeing the application meets required standards, regulatory compliance, and all safety and security requirements is the responsibility of the Buyer. These resources are subject to change without notice.

Electrical Characteristics

Maximum Ratings (@ T_A = 25°C, Unless otherwise specified)

| Parameters | Value | Unit |
|---|------------|-------|
| V _{RGS} Reverse Gate Source and Gate Drain Voltage | -50 | V |
| I _{FG} Continuous Forward Gate Current | 50 | mA |
| P _D Continuous Device Power Dissipation | 250 | mW |
| P Power Derating | 4.3 | mW/°C |
| T _J Operating Junction Temperature | -55 to 150 | °C |
| T _{STG} Storage Temperature | -65 to 200 | °C |

Static Characteristics (@ T_A = 25°C, Unless otherwise specified)

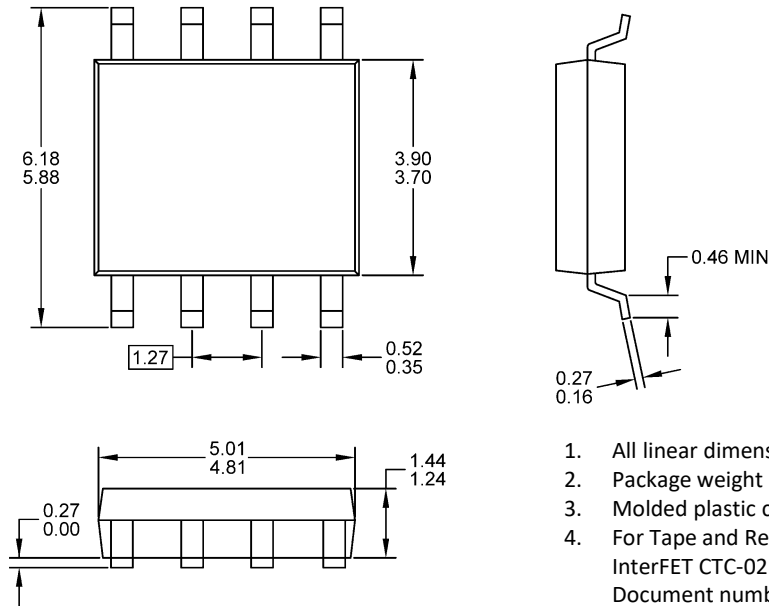
| Parameters | Conditions | IFN5911 | | IFN5912 | | Unit |
|---|--|---------|------|---------|------|------|
| | | Min | Max | Min | Max | |
| V _{(BR)GSS} Gate to Source Breakdown Voltage | I _G = -1μA, V _{DS} = 0V | -25 | | -25 | | V |
| I _{GSS} Gate to Source Reverse Current | V _{GS} = -15V, V _{DS} = 0V, T _A = 25°C | | -100 | | -100 | pA |
| | V _{GS} = -15V, V _{DS} = 0V, T _A = 150°C | | -250 | | -250 | nA |
| I _G Gate Operating Current | V _{DG} = 10V, I _D = 5mA, T _A = 25°C | | -100 | | -100 | pA |
| | V _{DG} = 10V, I _D = 5mA, T _A = 125°C | | -100 | | -100 | nA |
| V _{GS(OFF)} Gate to Source Cutoff Voltage | V _{DS} = 10V, I _D = 1nA | -1 | -5 | -1 | -5 | V |
| V _{GS} Gate Source Voltage | V _{DS} = 10V, I _D = 5mA | -0.3 | -4 | -0.3 | -4 | V |
| I _{DSS} Drain to Source Saturation Current | V _{DS} = 10V, V _{GS} = 0V (Pulsed) | 7 | 40 | 7 | 40 | mA |

Dynamic Characteristics (@ T_A = 25°C, Unless otherwise specified)

| Parameters | Conditions | IFN5911 | | IFN5912 | | Unit |
|--|--|---------|-------|---------|-------|--------|
| | | Min | Max | Min | Max | |
| G _{FS} Forward Transconductance | V _{DS} = 10V, I _D = 5mA, f = 1kHz | 3000 | 10000 | 3000 | 10000 | μS |
| | V _{DS} = 10V, I _D = 5mA, f = 100MHz | 3000 | 10000 | 3000 | 10000 | μS |
| G _{OS} Output Conductance | V _{DS} = 10V, I _D = 5mA, f = 1kHz | | 100 | | 100 | μS |
| | V _{DS} = 10V, I _D = 5mA, f = 100MHz | | 150 | | 150 | μS |
| C _{iss} Input Capacitance | V _{DS} = 10V, I _D = 5mA, f = 1MHz | | 5 | | 5 | pF |
| C _{rss} Reverse Capacitance | V _{DS} = 10V, I _D = 5mA, f = 1MHz | | 1.2 | | 1.2 | pF |
| NF Noise Figure | V _{DS} = 10V, I _D = 5mA, f = 10Hz, R _G = 100KΩ | | 1 | | 1 | dB |
| e _n Equivalent Circuit Input Noise Voltage | V _{DS} = 10V, I _D = 5mA, f = 10kHz | | 20 | | 20 | nV/√Hz |
| I _{G1} - I _{G2} Differential Gate Current | V _{DS} = 10V, I _D = 5mA, T _A = 125°C | | 20 | | 20 | nA |
| I _{DSS1} /I _{DSS2} Saturation Drain Current Ratio | V _{DS} = 10V, V _{GS} = 0V | 0.95 | 1 | 0.95 | 1 | - |
| V _{GS1} - V _{GS2} Differential Gate Source Voltage | V _{DS} = 10V, I _D = 5mA | | 10 | | 15 | mV |
| V _{GS1} - V _{GS2} / ΔT Differential Gate Source Voltage with Temperature | V _{DS} = 10V, I _D = 5mA, T _A = -55°C, T _B = 25°C | | 2.5 | | 5 | mV/°C |
| | T _A = 25°C, T _B = 125°C | | 2 | | 4 | mV/°C |
| g _{fs1} /g _{fs2} Transconductance Ratio | V _{DS} = 10V, I _D = 5mA | 0.95 | 1 | 0.95 | 1 | - |

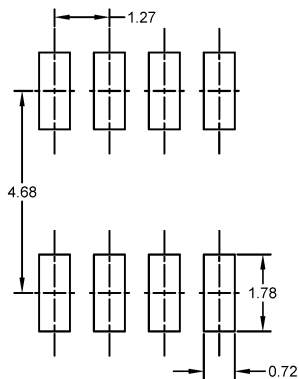
SOIC8 Mechanical and Layout Data

Package Outline Data



1. All linear dimensions are in millimeters.
2. Package weight approximately 0.21 grams
3. Molded plastic case UL 94V-0 rated
4. For Tape and Reel specifications refer to InterFET CTC-021 Tape and Reel Specification, Document number: IF39002
5. Bulk product is shipped in standard ESD shipping material
6. Refer to JEDEC standards for additional information.

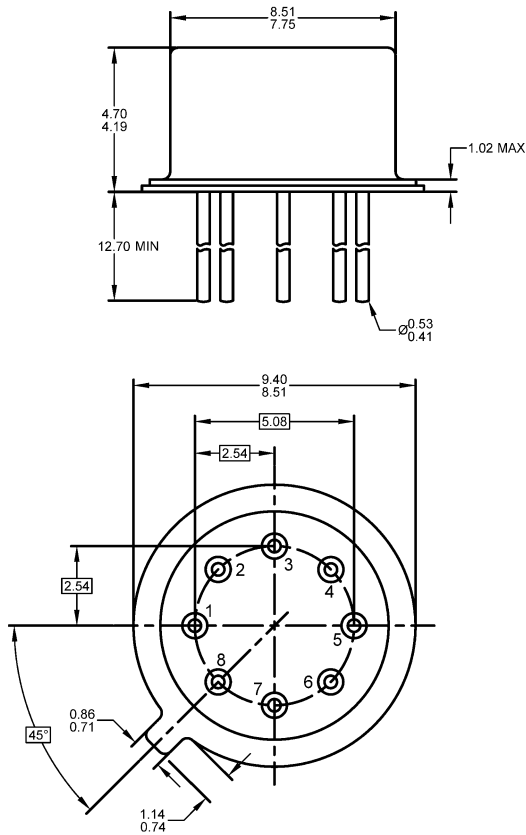
Suggested Pad Layout



1. All linear dimensions are in millimeters.
2. The suggested land pattern dimensions have been provided for reference only. A more robust pattern may be desired for wave soldering.

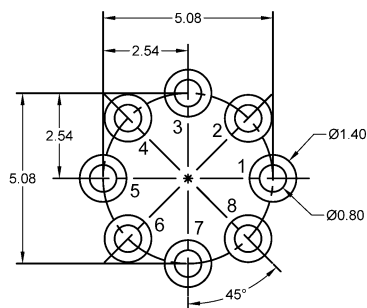
TO-78 Mechanical and Layout Data

Package Outline Data



1. All linear dimensions are in millimeters.
2. Eight leaded device. Not all leads are shown in drawing views.
3. Some package configurations will not populate pin 8 and/or pin 7.
4. Package weight approximately 0.44 grams
5. Bulk product is shipped in standard ESD shipping material
6. Refer to JEDEC standards for additional information.

Suggested Through-Hole Layout



1. All linear dimensions are in millimeters.
2. The suggested land pattern dimensions have been provided as a straight lead reference only. A more robust pattern may be desired for wave soldering and/or bent lead configurations.